Docket No.: M4065.0151/P151-B
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#78 Amdt
M. Brunson
2/12/03

In re Patent Application of:
Vishnu K. Agarwal, et al.

Application No.: 09/930,958

Group Art Unit: 2814

Filed: August 17, 2001

Examiner: Theresa T. Doan

For: MULTILAYER ELECTRODE FOR A FERROELECTRIC CAPACITOR

AMENDMENT

BOX: NON-FEE AMENDMENT
Commissioner for Patents
Washington, DC 20231

Dear Sir:

Responsive to the Office Action dated November 4, 2002, please amend the above-captioned application as follows:

IN THE CLAIMS:

Please cancel claims 56, 59, 61-62 and 72-123.

Please rewrite claims 55 and 60.

55. (amended) A memory cell, comprising:

a substrate;

a transistor including a gate on said substrate and a source/drain region in said substrate disposed adjacent to said gate;